74HC238; 74HCT238

3-to-8 line decoder/demultiplexer Rev. 03 — 16 July 2007

Product data sheet

1. **General description**

74HC238 and 74HCT238 are high-speed Si-gate CMOS devices and are pin compatible with Low-Power Schottky TTL (LSTTL).

The 74HC238/74HCT238 decoders accept three binary weighted address inputs (A0, A1, A2) and when enabled, provide 8 mutually exclusive active HIGH outputs (Y0 to Y7). The 74HC238/74HCT238 features three enable inputs: two active LOW (E1 and E2) and one active HIGH (E3). Every output will be LOW unless E1 and E2 are LOW and E3 is HIGH. This multiple enable function allows easy parallel expansion of the "238" to a 1-to-32 (5 lines to 32 lines) decoder with just four "238" ICs and one inverter. The "238" can be used as an eight output demultiplexer by using one of the active LOW enable inputs as the data input and the remaining enable inputs as strobes. Unused enable inputs must be permanently tied to their appropriate active HIGH or LOW state.

The 74HC238/74HCT238 is similar to the 74HC138/74HCT138 but has non-inverting outputs.

Features 2.

- Demultiplexing capability
- Multiple input enable for easy expansion
- Ideal for memory chip select decoding
- Active HIGH mutually exclusive outputs
- Multiple package options
- Complies with JEDEC standard no. 7A
- ESD protection:
 - HBM JESD22-A114E exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
- Specified from -40 °C to +85 °C and from -40 °C to +125 °C



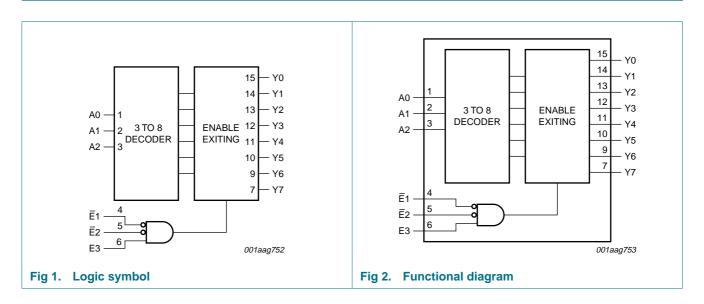
2 of 18

Ordering information

Table 1. **Ordering information**

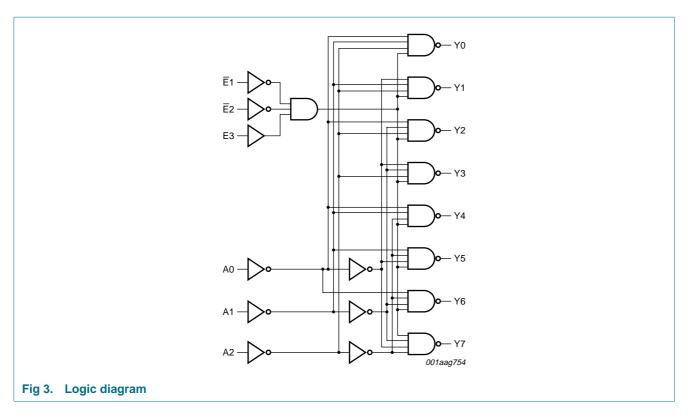
Type number	Package			
	Temperature range	Name	Description	Version
74HC238N	-40 °C to +125 °C	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4
74HC238D	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HC238DB	–40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads; body width 5.3 mm	SOT338-1
74HC238PW	–40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
74HC238BQ	–40 °C to +125 °C	DHVQFN16	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 \times 3.5 \times 0.85 mm	SOT763-1
74HCT238N	–40 °C to +125 °C	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4
74HCT238D	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HCT238DB	–40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads; body width 5.3 mm	SOT338-1
74HCT238PW	–40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
74HCT238BQ	–40 °C to +125 °C	DHVQFN16	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body $2.5\times3.5\times0.85$ mm	SOT763-1

Functional diagram



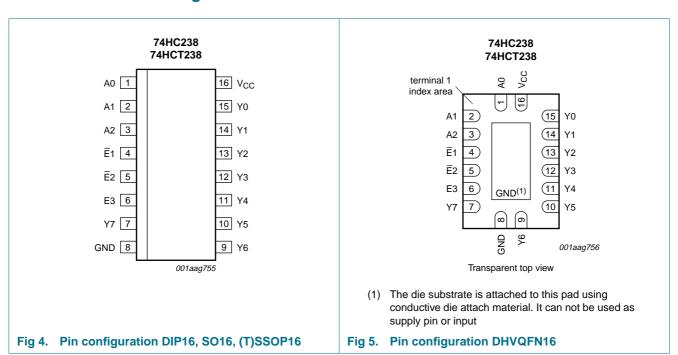
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3 of 18



Pinning information

5.1 Pinning



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5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
A[0:2]	1, 2, 3	address input
E1	4	enable input (active LOW)
E2	5	enable input (active LOW)
E3	6	enable input (active HIGH)
Y[0:7]	15, 14, 13, 12, 11, 10, 9, 7	output (active HIGH)
GND	8	ground (0 V)
V _{CC}	16	supply voltage

6. Functional description

Table 3. Function table[1]

Inputs						Outp	Outputs								
Ē1	E2	E3	A0	A1	A2	Y0	Y1	Y2	Y3	Y4	Y5	Y6	Y7		
Н	Χ	X	X	X	X	L	L	L	L	L	L	L	L		
Χ	Н	Х	X	Х	Х	L	L	L	L	L	L	L	L		
Χ	Χ	L	Χ	Χ	Χ	L	L	L	L	L	L	L	L		
L	L	Н	L	L	L	Н	L	L	L	L	L	L	L		
L	L	Н	Н	L	L	L	Н	L	L	L	L	L	L		
L	L	Н	L	Н	L	L	L	Н	L	L	L	L	L		
L	L	Н	Н	Н	L	L	L	L	Н	L	L	L	L		
L	L	Н	L	L	Н	L	L	L	L	Н	L	L	L		
L	L	Н	Н	L	Н	L	L	L	L	L	Н	L	L		
L	L	Н	L	Н	Н	L	L	L	L	L	L	Н	L		
L	L	Н	Н	Н	Н	L	L	L	L	L	L	L	Н		

^[1] H = HIGH voltage level;

L = LOW voltage level;

X = don't care.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7	V
I _{IK}	input clamping current	$V_I < -0.5 \text{ V or } V_I > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> _	±20	mA
I _{OK}	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> _	±20	mA
Io	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±25	mA
I _{CC}	supply current		-	50	mA
I_{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	DIP16 package	[2] -	750	mW
		SO16, SSOP16, TSSOP16 and DHVQFN16 packages	<u>[3]</u> _	500	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		74HC238	3	7	8	Unit	
			Min	Тур	Max	Min	Тур	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V_{I}	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
Vo	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	-	+125	-40	-	+125	°C
$\Delta t/\Delta V$	input transition rise	$V_{CC} = 2.0 \text{ V}$	-	-	625	-	-	-	ns/V
a	and fall rate	V _{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0 \text{ V}$	-	-	83	-	-	-	ns/V

^[2] For DIP16 packages: above 70 °C the value of Ptot derates linearly at 12 mW/K.

^[3] For SO16 packages: above 70 °C the value of P_{tot} derates linearly at 8 mW/K.
For SSOP16 and TSSOP16 packages: above 60 °C the value of P_{tot} derates linearly at 5.5 mW/K.
For DHVQFN16 packages: above 60 °C the value of P_{tot} derates linearly at 4.5 mW/K.

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		–40 °C to	o +85 °C	–40 °C to	+125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC238	8									
V _{IH}	HIGH-level	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
	input voltage	V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V_{IL}	LOW-level	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
	input voltage	V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V _{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_O = -20 \mu A$; $V_{CC} = 2.0 \text{ V}$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -20 \mu A$; $V_{CC} = 4.5 V$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -20 \mu A$; $V_{CC} = 6.0 \text{ V}$	5.9	6.0	-	5.9	-	5.9	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.98	4.32	-	3.84	-	3.7	-	V
		$I_{O} = -5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.48	5.81	-	5.34	-	5.2	-	V
V _{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_O = 20 \mu A; V_{CC} = 2.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \mu A; V_{CC} = 6.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	0.15	0.26	-	0.33	-	0.4	V
		$I_{O} = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.26	-	0.33	-	0.4	V
I _I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0 \text{ V}$	-	-	8.0	-	80	-	160	μΑ
Cı	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT2	38									
V_{IH}	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	1.6	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	1.2	8.0	-	0.8	-	0.8	V
V _{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -4.0 \text{ mA}$	3.98	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	Ι _O = 20 μΑ	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA	-	0.16	0.26	-	0.33	-	0.4	V
Iį	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$	-	-	±0.1	-	±1.0	-	±1.0	μΑ

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 Table 6.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		–40 °C to	+85 °C	–40 °C to	Unit	
			Min	Тур	Max	Min	Max	Min	Max	
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 \text{ V}$; $I_O = 0 \text{ A}$	-	-	8.0	-	80	-	160	μΑ
Δl _{CC}	additional supply current	per input pin; $V_{I} = V_{CC} - 2.1 \text{ V};$ other inputs at V_{CC} or GND; $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V};$ $I_{O} = 0 \text{ A}$								
		An inputs	-	70	252	-	315	-	343	μΑ
		E1, E2 inputs	-	40	144	-	180	-	196	μΑ
		E3 input	-	145	522	-	653	-	711	μΑ
Cı	input capacitance		-	3.5	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

GND = 0 V; test circuit see Figure 8.

Symbol	Parameter	Conditions			25 °C			+125 °C	
				Min	Тур	Max	Max (85 °C)	Max (125 °C)	Unit
74HC238	3								
t _{pd}	propagation delay	An to Yn; see Figure 6	<u>[1]</u>						
		V _{CC} = 2.0 V		-	47	150	190	225	ns
		V _{CC} = 4.5 V		-	17	30	38	45	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	14	-	-	-	ns
		V _{CC} = 6.0 V		-	14	26	33	38	ns
		E3 to Yn; see Figure 6	<u>[1]</u>						
		V _{CC} = 2.0 V		-	52	160	200	240	ns
		V _{CC} = 4.5 V		-	19	32	40	48	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	16	-	-	-	ns
		V _{CC} = 6.0 V		-	15	27	34	41	ns
		En to Yn or see Figure 7	<u>[1]</u>						
		V _{CC} = 2.0 V		-	50	155	195	235	ns
		V _{CC} = 4.5 V		-	18	31	39	47	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	17	-	-	-	ns
		V _{CC} = 6.0 V		-	14	26	33	40	ns
t _t	transition time	see Figure 6 and Figure 7	[2]						
		V _{CC} = 2.0 V		-	19	75	95	110	ns
		$V_{CC} = 4.5 \text{ V}$		-	7	15	19	22	ns
		$V_{CC} = 6.0 \text{ V}$		-	6	13	16	19	ns
C _{PD}	power dissipation capacitance	per package; $V_I = GND$ to V_{CC}	[3]	-	72	-	-	-	pF

74HC_HCT238_3

 Table 7.
 Dynamic characteristics

GND = 0 V; test circuit see Figure 8.

Symbol	Parameter	Conditions		25 °C		–40 °C to	+125 °C		
				Min	Тур	Max	Max (85 °C)	Max (125 °C)	Unit
74HCT2	38								
t _{pd}	propagation delay	An to Yn; see Figure 6	<u>[1]</u>						
		$V_{CC} = 4.5 \text{ V}$		-	19	35	44	53	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	18	-	-	-	ns
		E3 to Yn; see Figure 6	<u>[1]</u>						
		$V_{CC} = 4.5 \text{ V}$		-	20	37	46	56	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	20	-	-	-	ns
		En to Yn or see Figure 7	<u>[1]</u>						
		$V_{CC} = 4.5 \text{ V}$		-	20	35	44	53	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 15 \text{ pF}$		-	21	-	-	-	ns
t _t	transition time	V _{CC} = 4.5 V; see <u>Figure 6</u> and <u>Figure 7</u>	[2]	-	7	15	19	22	ns
C_{PD}	power dissipation capacitance	per package; V _I = GND to V _{CC} – 1.5 V	[3]	-	76	-	-	-	pF

- [1] t_{pd} is the same as t_{PHL} and t_{PLH} .
- [2] t_t is the same as t_{THL} and t_{TLH} .
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW):

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

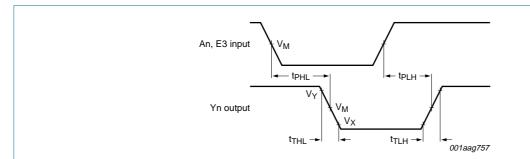
 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\sum (C_L \times V_{CC}^2 \times f_o) = \text{sum of outputs.}$

11. Waveforms



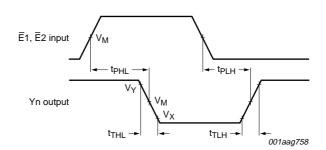
Measurement points are given in <u>Table 8</u>.

 $V_{\mbox{\scriptsize OL}}$ and $V_{\mbox{\scriptsize OH}}$ are typical voltage output levels that occur with the output load.

Fig 6. Input (An, E3) to output (Yn) propagation delays and output transition times

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9 of 18



Measurement points are given in Table 8.

 $\ensuremath{V_{OL}}$ and $\ensuremath{V_{OH}}$ are typical voltage output levels that occur with the output load.

Fig 7. Input ($\overline{E}1$, $\overline{E}2$) to output (Yn) propagation delays and output transition times

Table 8. **Measurement points**

Туре	Input	Output							
	V _M	V _M	V _X	V _Y					
74HC238	0.5V _{CC}	0.5V _{CC}	0.1V _{CC}	0.9V _{CC}					
74HCT238	1.3 V	1.3 V	0.1V _{CC}	0.9V _{CC}					

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10 of 18

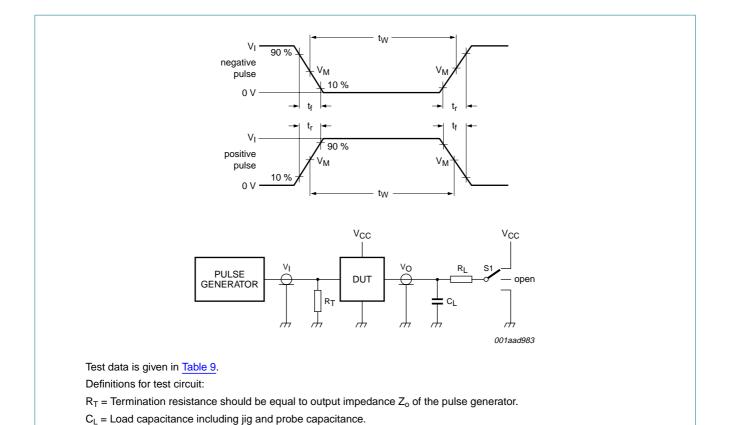


Fig 8. Load circuit for measuring switching times

R_L = Load resistance. S1 = Test selection switch

Table 9. **Test data**

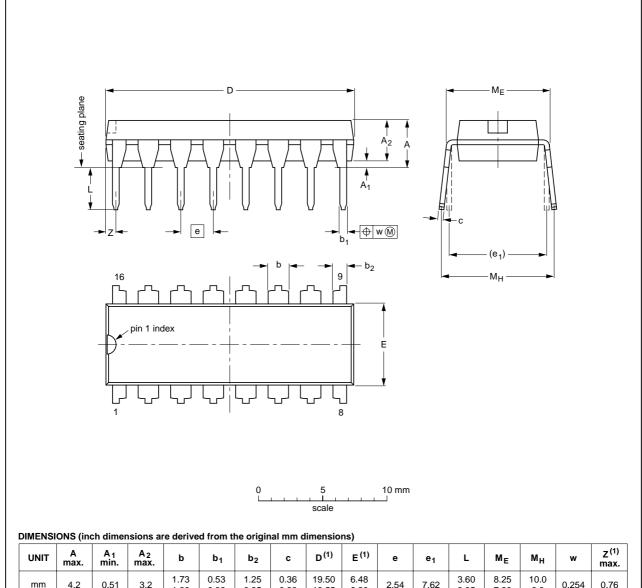
Туре	Input I		Load	S1 position	
	V_{l} t_{r}, t_{f}		CL	R _L	t _{PHL} , t _{PLH}
74HC238	V_{CC}	6 ns	15 pF, 50 pF	1 kΩ	open
74HCT238	3 V	6 ns	15 pF, 50 pF	1 kΩ	open

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12. Package outline

DIP16: plastic dual in-line package; 16 leads (300 mil)

SOT38-4



UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	b ₂	С	D ⁽¹⁾	E ⁽¹⁾	е	e ₁	L	ME	M _H	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.30	0.53 0.38	1.25 0.85	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	0.76
inches	0.17	0.02	0.13	0.068 0.051	0.021 0.015	0.049 0.033	0.014 0.009	0.77 0.73	0.26 0.24	0.1	0.3	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.03

1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

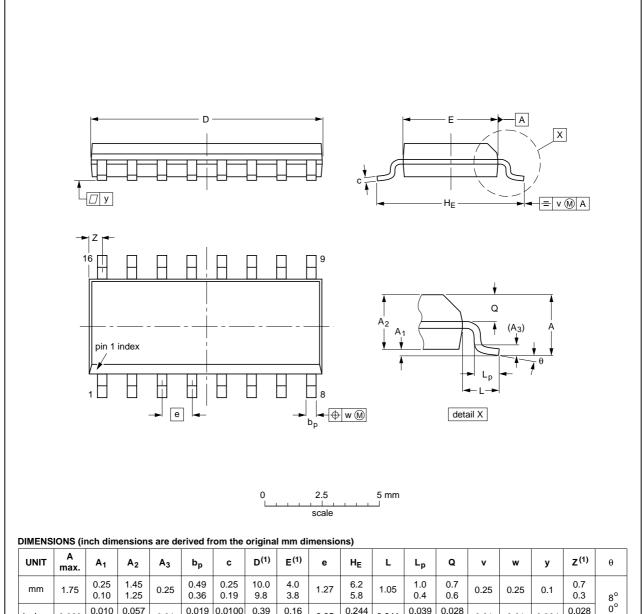
OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT38-4						95-01-14 03-02-13	

Fig 9. Package outline SOT38-4 (DIP16)

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SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01		0.0100 0.0075	0.39 0.38	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.020	0.01	0.01	0.004	0.028 0.012	0°

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

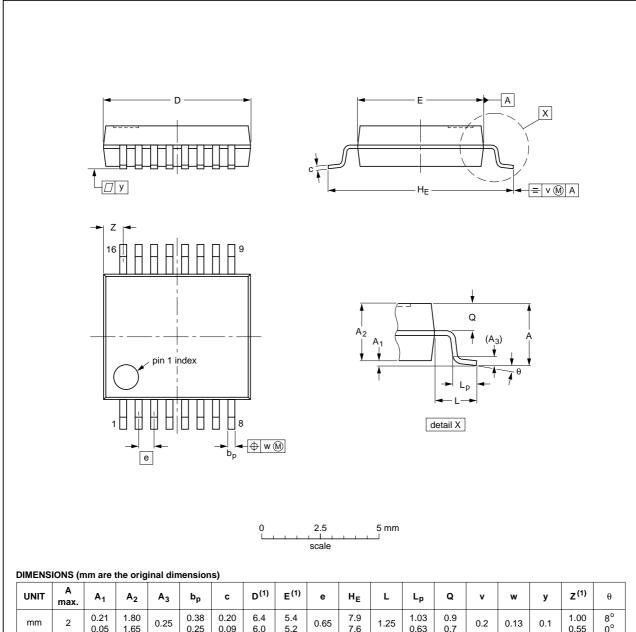
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VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT109-1	076E07	MS-012				99-12-27 03-02-19	

Fig 10. Package outline SOT109-1 (SO16)

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SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm

SOT338-1



ι	JNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
	mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.00 0.55	8° 0°

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC JEITA		PROJECTION	ISSUE DATE	
SOT338-1		MO-150			99-12-27 03-02-19	

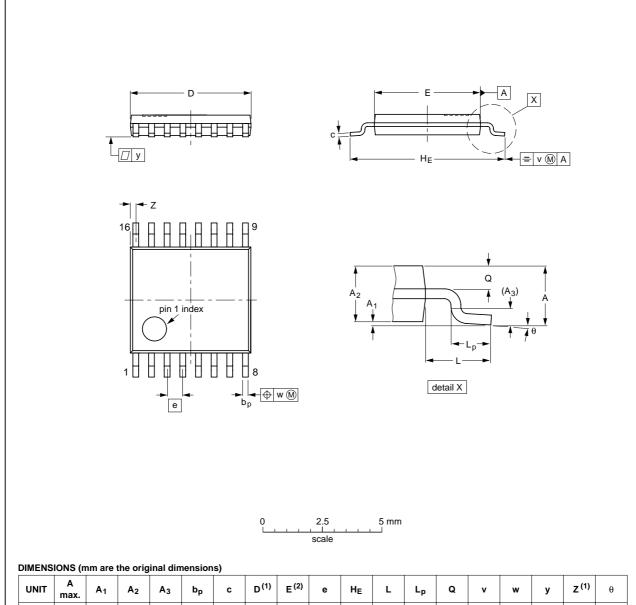
Fig 11. Package outline SOT338-1 (SSOP16)

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TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1

14 of 18



UNIT	A max.	A ₁	A ₂	А3	bp	C	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8° 0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	RENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT403-1		MO-153			99-12-27 03-02-18	

Fig 12. Package outline SOT403-1 (TSSOP16)

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15 of 18

DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; SOT763-1 16 terminals; body 2.5 x 3.5 x 0.85 mm

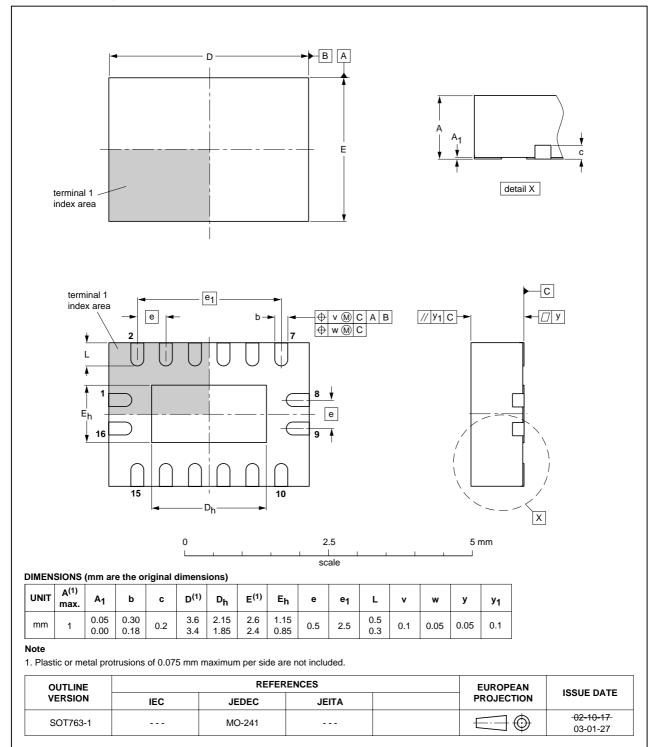


Fig 13. Package outline SOT763-1 (DHVQFN16)

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13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT238_3	20070716	Product data sheet	-	74HC_HCT238_CNV_2
Modifications:		of this data sheet has been of NXP Semiconductors.	n redesigned to co	mply with the new identity
	 Legal texts 	have been adapted to the	new company nam	e where appropriate.
	 Added type 	number 74HC238BQ and	74HCT238BQ (DF	HVQFN16 package)
74HC_HCT238_CNV_2	19970828	Product specification	-	-

 74HC_HCT238_3
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 Product data sheet
 Rev. 03 − 16 July 2007
 16 of 18

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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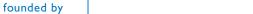
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17. Contents

1	General description
2	Features
3	Ordering information
4	Functional diagram 2
5	Pinning information
5.1	Pinning
5.2	Pin description
6	Functional description 4
7	Limiting values 5
8	Recommended operating conditions 5
9	Static characteristics 6
10	Dynamic characteristics
11	Waveforms
12	Package outline 11
13	Abbreviations
14	Revision history
15	Legal information
15.1	Data sheet status
15.2	Definitions
15.3	Disclaimers
15.4	Trademarks17
16	Contact information
17	Contents 18

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